

/ Descriptions

TO-251 N MOS

N-CHANNEL MOSFET in a TO-251 Plastic Package.

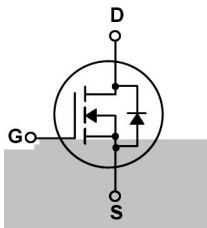
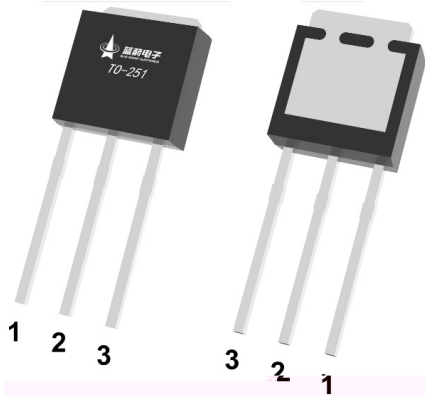
/ Features

Low gate charge, low crss, fast switching, HF Product.

/ Applications

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit**/ Pinning**

PIN1 G

PIN 2 D

PIN 3 S

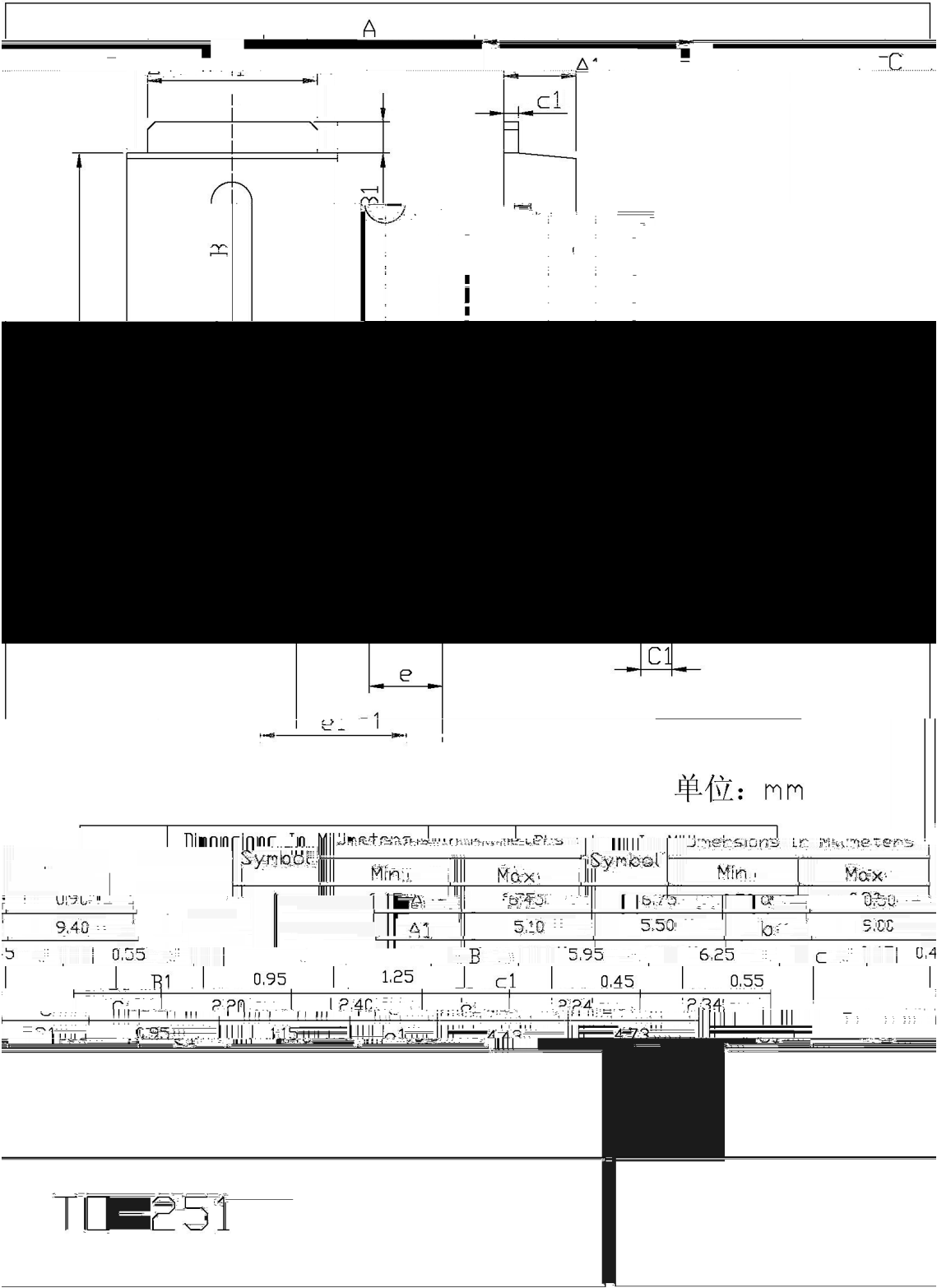
/ Marking

See Marking Instructions.

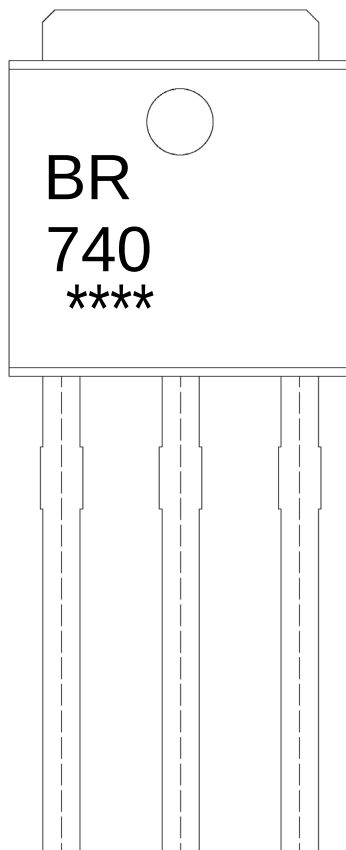
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	400	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	10	A
	$I_D(T_c=100^\circ\text{C})$	6.3	A
Pulsed Drain Current	I_{DM}	40	A
Gate-Source Voltage	V_{GS}	± 30	V
Avalanche Current	I_{AR}	10	A
Single Pulsed Avalanche Energy	E_{AS}	450	mJ
Repetitive Avalanche Energy	E_{AR}	13.4	mJ
Total Power Dissipation	$P_D(T_c=25^\circ\text{C})$	134	W

Junction and Storage Temperature: $-55^\circ\text{C} \sim 175^\circ\text{C}$

/ Package Dimensions



/ Marking Instructions



BR

740

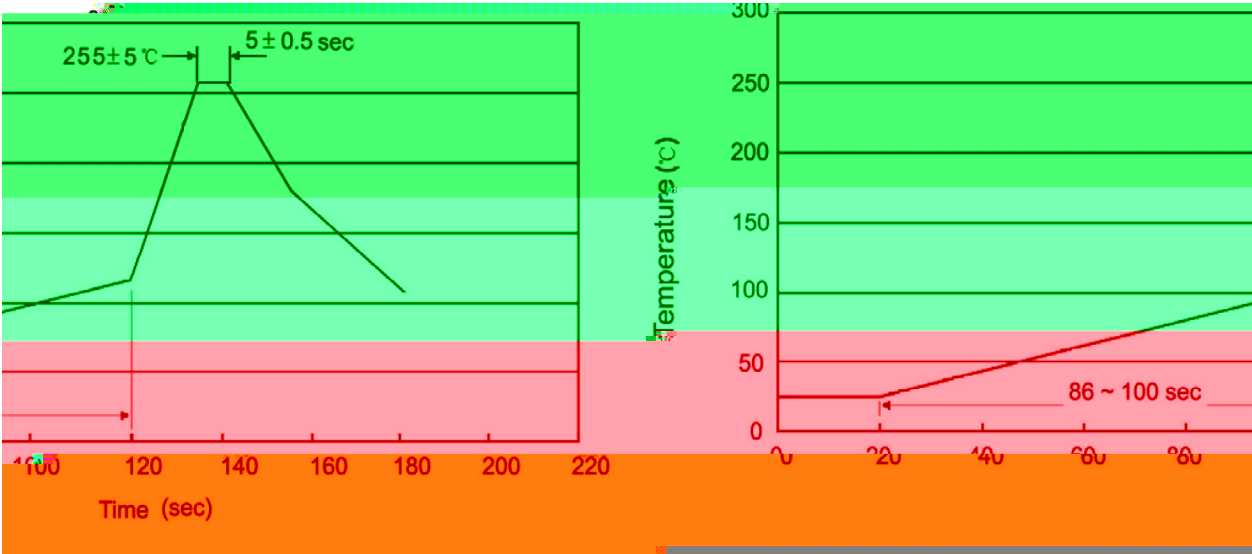
Note:

BR: Company Code

740: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension			(unit mm ³)
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box	